



国际知名大学原版教材

—— 信息技术学科与电气工程学科系列

31

Microsensors, MEMS, and Smart Devices

微传感器、微机电系统和灵巧器件

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清华大学出版社

Julian W. Gardner, Vijay K. Varadan, Osama O. Awadelkarim
Microsensors, MEMS, and Smart Devices

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国际知名大学原版教材

——信息技术学科与电气工程学科系列

出版说明

郑大钟

清华大学信息科学与技术学院

当前,在我国的高等学校中,教学内容和课程体系的改革已经成为教学改革中的一个非常突出的问题,而为数不少的课程教材中普遍存在的“课程体系老化,内容落伍时代,本研层次不清”的现象又是其中的急需改变的一个重要方面。同时,随着科教兴国方针的贯彻落实,要求我们进一步转变观念扩大视野,使教学过程适应以信息技术为先导的技术革命和我国社会主义市场经济体制的需要,加快教学过程的国际化进程。在这方面,系统地研究和借鉴国外知名大学的相关教材,将会对推进我们的课程改革和推进我国大学教学的国际化进程,乃至对我们一些重点大学建设国际一流大学的努力,都将具有重要的借鉴推动作用。正是基于这种背景,我们决定在国内推出信息技术学科和电气工程学科国外知名大学原版系列教材。

本系列教材的组编将遵循如下的几点基本原则。(1)书目的范围限于信息技术学科和电气工程学科所属专业的技术基础课和主要的专业课。(2)教材的范围选自于具有较大影响且为国外知名大学所采用的教材。(3)教材属于在近5年内所出版的新书或新版书。(4)教材适合于作为我国大学相应课程的教材或主要教学参考书。(5)每本列选的教材都须经过国内相应领域的资深专家审看和推荐。(6)教材的形式直接以英文原版形式印刷出版。

本系列教材将按分期分批的方式组织出版。为了便于使用本系列教材的相关教师和学生从学科和教学的角度对其在体系和内容上的特点和特色有所了解,在每本教材中都附有所约请的相关领域资深教授撰写的影印版序言。此外,出于多样化的考虑,对于某些基本类型的课程,我们还同时列选了多于一本的不同体系、不同风格 and 不同层次的教材,以供不同要求和不同学时的同类课程的选用。

本系列教材的读者对象为信息技术学科和电气工程学科所属各专业的本科生,同时兼顾其他工程学科专业的本科生或研究生。本系列教材,既可采用作为相应课程的教材或教学参考书,也可提供作为工作于各个技术领域的工程师和技术人员的自学读物。

组编这套国外知名大学原版系列教材是一个尝试。不管是书目确定的合理性,教材选择的恰当性,还是评论看法的确切性,都有待于通过使用和实践来检验。感谢使用本系列教材的广大教师和学生的支持。期望广大读者提出意见和建议。

Microsensors, MEMS, and Smart Devices

影印版序

从 20 世纪 90 年代中期以来, Microsensors (微传感器) 以及在微传感器基础上发展起来的 MEMS (微机电系统) 已经逐渐被人们所熟悉, 并越来越受到重视, 目前已成为国际上的研究热点。由于认识到发展微传感器及 MEMS 是信息化进程的重要内容, 它们在现代工业、农业、交通、生物、医学、航空、航天、国防以及日常生活和家电等领域都有重要与广泛的应用, 因此微传感器及 MEMS 也同样成为我国信息科技与产业的重点研究与发展对象。

微传感器和 MEMS 与现代微纳米科技密切相关, 它们的制作技术就是在现代微电子制作技术的基础上发展形成的。微电子制作技术是一种二维的平面微加工技术, 而微传感器和 MEMS 则是三维的立体加工技术。微传感器与微机电系统是一门与电子学、物理学、化学、生物学、医学、材料科学等多学科交叉的高新技术, 而微动力学、微静力学、微流体力学、微传热学、微光学、微声学、生物化学、微分析等都是发展微传感器与微机电系统必须研究的课题。本书的目的就是向大家阐述这方面的知识、理论与技术。

本书内容丰富, 主要论述微传感器及微机电系统的结构、原理、特性、制作方法与工艺技术。例如在材料与制作技术方面, 介绍了微电子学中各种薄膜材料和制备方法, 以及重要的微电子工艺技术 (标准的硅平面工艺), 讲述了两类重要的硅三维加工技术, 即体微加工技术与表面微加工技术。此外, 重点介绍了三维光刻技术。在器件与系统方面, 论述了热、辐射、力、声、磁、生物等多类传感器的结构、原理与特性, 并且重点介绍了叉指式声表面波传感系统以及智能型传感系统。这些内容都是目前研究的前沿课题。

本书作者是来自于英国和美国的三位教授, 他们在微传感器、微机电系统以及智能 (灵巧) 器件方面都有深厚的研究基础和教学经验, 都发表过大量的学术论文并著有多部有关书籍, 是该领域的知名学者。本著作的写作方法也颇具特色, 避免了过多的推导, 而着重于物理概念的阐述, 不但使那些对本著作内容比较熟悉的微电子学与电子工程的学生, 而且对于其他专业, 如机械工程、物理学、材料科学甚至生物科学的学生都能很好地理解和接受。

该著作不但可以作为相关专业大学高年级学生和研究生教材与参考书, 而且对于在微传感器与微机电系统方面感兴趣的科学家、工程师、技术人员都是很有价值的参考书。

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2004 年 1 月

Preface

The miniaturisation of sensors has been made possible by advances in the technologies originating in the semiconductor industry, and the emergent field of microsensors has grown rapidly during the past 10 years. The term *microsensor* is now commonly used to describe a *miniature* device that converts a nonelectrical quantity, such as pressure, temperature, or gas concentration, into an electrical signal. This book basically reports on the recent developments in, firstly, the miniaturisation of a sensor to produce a microsensor; secondly, the integration of a microsensor and its microelectronic circuitry to produce a so-called *smart sensor*; and thirdly, the integration of a microsensor, a microactuator, and their microelectronic circuitry to produce a *microsystem*.

Many of the microsystems being fabricated today employ silicon microtechnology and are called *microelectricalmechanical systems* or *MEMS* in short. Consequently, the first part of this book concentrates on the materials and processes required to make different kinds of microsensors and MEMS devices. The book aims to make the reader familiar with these processes and technologies. Of course, most of these technologies have been derived from those currently employed in the semiconductor industry and so we also review the standard microelectronics technologies used today to produce silicon wafers, process them into discrete devices or very large-scale integrated circuits, and package them. These *must* be used when the microelectronics is being integrated to form either a *hybrid* device, such as a *multichip module* (MCM), or a fully integrated device, such as a smart sensor. We then describe the new techniques that have been developed to make microsensors and microactuators, such as bulk and surface silicon micromachining, followed by the emerging technology of microstereolithography that can be used to form true three-dimensional micromechanical structures.

The reader is now fully prepared for our description of the different types of microsensors made today and the way in which they can be integrated with the microelectronics to make a smart device (e.g. an electronic eye, electronic nose, or microtweezers) or integrated with a microactuator to make a microsystem. Several of these chapters have been dedicated to the important topic of IDT microsensors, that is, surface acoustic wave devices that possess an interdigital transducer and so can be used to sense a wide variety of signals from mechanical to chemical. This type of microsensor is attractive, not only because it offers both high sensitivity and compatibility with the microelectronics industry but also because it can be operated and even powered by a wireless radio frequency link. The latter overcomes the initial constraints of communicating with small, low energy budget, and even mobile MEMS – now referred to as micromachines!

Our aim has been to write a book that serves as a text suitable both for an advanced undergraduate course and for a master's programme. Some of the material may well be familiar to students of electrical engineering or electronics. However, our comprehensive treatment will make it equally familiar to mechanical engineers, physicists, and materials scientists.

We have provided more than 10 appendices to aid the reader and serve as a source of reference material. These appendices explain the key abbreviations and terms used in the book, provide suggestions for further reading, give tables of the properties of materials important in microsensors and MEMS, and finally provide a list of the web sites of major journals and active institutions in this field. In addition, this book is aimed to be a valuable reference text for anyone interested in the field of microsensors and MEMS (whether they are an engineer, a scientist, or a technologist) and the technical references at the end of each chapter will enable such readers to trace back the original material.

Finally, much of the material for this book has been taken from short courses prepared by the authors and presented to students and industrialists in Europe, North America, and the Far East. Their many valuable comments have helped us to craft this book into its final form and so we owe them our thanks. The authors are also grateful to many of their students and colleagues, in particular Professor Vasundara V. Varadan, Dr. K. A. Jose, Dr. P. Xavier, Mr. S. Gangadharan, Mr. William Suh, and Mr. H. Subramanian for their valuable contributions.

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September 2001

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Vijay K. Varadan is Alumni Distinguished Professor of Engineering at the Pennsylvania State University, USA. He received his Ph.D. degree in Engineering Science from the Northwestern University in 1974. He has a B.E. in Mechanical Engineering (1964) from the University of Madras, India and an M.S. in Engineering Mechanics (1969) from the Pennsylvania State University. After serving on the faculty of Cornell University and Ohio State University, he joined the Pennsylvania State University in 1983, where he is currently Alumni Distinguished Professor of Engineering science, Mechanics, and Electrical Engineering. He is involved in all aspects of wave-material interaction, optoelectronics, microelectronics, photonics, microelectromechanical systems (MEMS): nanoscience and technology, carbon nanotubes, microstereolithography smart materials and structures; sonar, radar, microwave, and optically absorbing composite media; EMI, RFI, EMP, and EMF shielding materials; piezoelectric, chiral, ferrite, and polymer composites and conducting polymers; and UV conformal coatings, tunable ceramics materials and substrates, and electronically steerable antennas. He is the Editor of the *Journal of Wave-Material Interaction* and the Editor-in-Chief of the *Journal of Smart Materials and Structures* published by the Institute of Physics, UK. He has authored more than 400 technical papers and six books. He has eight patents pertinent to conducting polymers, smart structures and smart antennas, and phase shifters.

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Contents

Preface	xiii
About the Authors	xv
Acknowledgments	xvii
1 Introduction	1
1.1 Historical Development of Microelectronics	1
1.2 Evolution of Microsensors	2
1.3 Evolution of MEMS	5
1.4 Emergence of Micromachines	7
References	8
2 Electronic Materials and Processing	9
2.1 Introduction	9
2.2 Electronic Materials and their Deposition	9
2.2.1 Oxide Film Formation by Thermal Oxidation	10
2.2.2 Deposition of Silicon Dioxide and Silicon Nitride	11
2.2.3 Polysilicon Film Deposition	15
2.3 Pattern Transfer	15
2.3.1 The Lithographic Process	15
2.3.2 Mask Formation	18
2.3.3 Resist	18
2.3.4 Lift-off Technique	21
2.4 Etching Electronic Materials	22
2.4.1 Wet Chemical Etching	22
2.4.2 Dry Etching	23
2.5 Doping Semiconductors	27
2.5.1 Diffusion	30
2.5.2 Ion Implantation	31
2.6 Concluding Remarks	32
References	34
3 MEMS Materials and their Preparation	35
3.1 Overview	35
3.1.1 Atomic Structure and the Periodic Table	35

3.1.2 Atomic Bonding	40
3.1.3 Crystallinity	44
3.2 Metals	49
3.2.1 Physical and Chemical Properties	49
3.2.2 Metallisation	50
3.3 Semiconductors	52
3.3.1 Semiconductors: Electrical and Chemical Properties	52
3.3.2 Semiconductors: Growth and Deposition	54
3.4 Ceramic, Polymeric, and Composite Materials	58
References	59
 4 Standard Microelectronic Technologies	 61
4.1 Introduction	61
4.2 Wafer Preparation	63
4.2.1 Crystal Growth	63
4.2.2 Wafer Manufacture	66
4.2.3 Epitaxial Deposition	68
4.3 Monolithic Processing	70
4.3.1 Bipolar Processing	73
4.3.2 Characteristics of BJTs	82
4.3.3 MOS Processing	90
4.3.4 Characteristics of FETs	93
4.3.5 SOI CMOS Processing	97
4.4 Monolithic Mounting	99
4.4.1 Die Bonding and Wire Bonding	100
4.4.2 Tape-Automated Bonding	101
4.4.3 Flip TAB Bonding	103
4.4.4 Flip-Chip Mounting	103
4.5 Printed Circuit Board Technologies	104
4.5.1 Solid Board	104
4.5.2 Flexible Board	105
4.5.3 Plastic Moulded	107
4.6 Hybrid and MCM Technologies	108
4.6.1 Thick Film	108
4.6.2 Multichip Modules	108
4.6.3 Ball Grid Array	111
4.7 Programmable Devices And ASICs	112
References	116
 5 Silicon Micromachining: Bulk	 117
5.1 Introduction	117
5.2 Isotropic and Orientation-Dependent Wet Etching	118
5.3 Etch-Stop Techniques	124
5.3.1 Doping-Selective Etching (DSE)	124
5.3.2 Conventional Bias-Dependent BSE or Electrochemical Etch-Stop	126

5.3.3 Selective Etching of <i>n</i> -Type Silicon by Pulsed Potential Anodisation	131
5.3.4 Photovoltaic Electrochemical Etch-Stop Technique (PHET)	131
5.4 Dry Etching	134
5.5 Buried Oxide Process	137
5.6 Silicon Fusion Bonding	138
5.6.1 Wafer Fusion	138
5.6.2 Annealing Treatment	138
5.6.3 Fusion of Silicon-Based Materials	139
5.7 Anodic Bonding	140
5.8 Concluding Remarks	143
References	143
6 Silicon Micromachining: Surface	145
6.1 Introduction	145
6.2 Sacrificial Layer Technology	145
6.2.1 Simple Process	146
6.2.2 Sacrificial Layer Processes Utilising more than One Structural Layer	151
6.3 Material Systems in Sacrificial Layer Technology	155
6.3.1 Polycrystalline Silicon and Silicon Dioxide	156
6.3.2 Polyimide and Aluminum	156
6.3.3 Silicon Nitride/Polycrystalline Silicon and Tungsten/Silicon Dioxide	157
6.4 Surface Micromachining using Plasma Etching	158
6.5 Combined IC Technology and Anisotropic Wet Etching	162
6.6 Processes Using Both Bulk and Surface Micromachining	166
6.7 Adhesion Problems in Surface Micromachining	170
6.8 Surface Versus Bulk Micromachining	172
References	172
7 Microstereolithography for MEMS	173
7.1 Introduction	173
7.1.1 Photopolymerisation	174
7.1.2 Stereolithographic System	178
7.2 Microstereolithography	179
7.3 Scanning Method	181
7.3.1 Classical MSL	181
7.3.2 IH Process	182
7.3.3 Mass-IH Process	184
7.3.4 Super-IH Process	186
7.4 Two-photon MSL	189
7.5 Other MSL Approaches	192
7.6 Projection Method	193
7.6.1 Mask-Projection MSL	193
7.6.2 Dynamic Mask-Projection MSL	196

7.7 Polymeric MEMS Architecture with Silicon, Metal, and Ceramics	197
7.7.1 Ceramic MSL	197
7.7.2 Metallic Microstructures	202
7.7.3 Metal-Polymer Microstructures	205
7.7.4 Localised Electrochemical Deposition	206
7.8 Combined Silicon and Polymeric Structures	210
7.8.1 Architecture Combination by Photoforming Process	210
7.8.2 MSL Integrated with Thick Film Lithography	212
7.8.3 AMANDA Process	213
7.9 Applications	216
7.9.1 Microactuators Fabricated by MSL	216
7.9.2 Microconcentrator	218
7.9.3 Microdevices Fabricated by the AMANDA Process	220
7.10 Concluding Remarks	224
References	225
8 Microsensors	227
8.1 Introduction	227
8.2 Thermal Sensors	230
8.2.1 Resistive Temperature Microsensors	231
8.2.2 Microthermocouples	232
8.2.3 Thermodiodes and Thermotransistors	236
8.2.4 SAW Temperature Sensor	239
8.3 Radiation Sensors	240
8.3.1 Photoconductive Devices	241
8.3.2 Photovoltaic Devices	242
8.3.3 Pyroelectric Devices	244
8.3.4 Microantenna	245
8.4 Mechanical Sensors	247
8.4.1 Overview	247
8.4.2 Micromechanical Components and Statics	249
8.4.3 Microshuttles and Dynamics	251
8.4.4 Mechanical Microstructures	254
8.4.5 Pressure Microsensors	257
8.4.6 Microaccelerometers	263
8.4.7 Microgyrometers	266
8.4.8 Flow Microsensors	268
8.5 Magnetic Sensors	270
8.5.1 Magnetogalvanic Microsensors	272
8.5.2 Magnetoresistive Devices	274
8.5.3 Magnetodiodes and Magnetotransistors	275
8.5.4 Acoustic Devices and SQUIDS	277
8.6 Bio(chemical) Sensors	280
8.6.1 Conductimetric Devices	282
8.6.2 Potentiometric Devices	292
8.6.3 Others	296

8.7 Concluding Remarks	300
References	300
9 Introduction to SAW Devices	303
9.1 Introduction	303
9.2 Saw Device Development and History	303
9.3 The Piezoelectric Effect	306
9.3.1 Interdigital Transducers in SAW Devices	307
9.4 Acoustic Waves	308
9.4.1 Rayleigh Surface Acoustic Waves	308
9.4.2 Shear Horizontal Acoustic Waves	311
9.4.3 Love Surface Acoustic Waves	312
9.5 Concluding Remarks	314
References	316
10 Surface Acoustic Waves in Solids	319
10.1 Introduction	319
10.2 Acoustic Wave Propagation	320
10.3 Acoustic Wave Propagation Representation	321
10.4 Introduction to Acoustics	321
10.4.1 Particle Displacement and Strain	321
10.4.2 Stress	323
10.4.3 The Piezoelectric Effect	324
10.5 Acoustic Wave Propagation	325
10.5.1 Uniform Plane Waves in a Piezoelectric Solid: Quasi-Static Approximation	325
10.5.2 Shear Horizontal or Acoustic Plate Modes	328
10.5.3 Love Modes	330
10.6 Concluding Remarks	334
References	334
11 IDT Microsensor Parameter Measurement	337
11.1 Introduction to IDT SAW Sensor Instrumentation	337
11.2 Acoustic Wave Sensor Instrumentation	337
11.2.1 Introduction	337
11.3 Network Analyser and Vector Voltmeter	338
11.4 Analogue (Amplitude) Measuring System	339
11.5 Phase Measurement System	340
11.6 Frequency Measurement System	341
11.7 Acoustic Wave Sensor Output Frequency Translation	342
11.8 Measurement Setup	343
11.9 Calibration	344
References	345
12 IDT Microsensor Fabrication	347
12.1 Introduction	347
12.2 Saw-IDT Microsensor Fabrication	347

12.2.1 Mask Generation	347
12.2.2 Wafer Preparation	348
12.2.3 Metallisation	349
12.2.4 Photolithography	350
12.2.5 Wafer Dicing	352
12.3 Deposition of Waveguide Layer	353
12.3.1 Introduction	353
12.3.2 TMS PECVD Process and Conditions	354
12.4 Concluding Remarks	358
References	358
13 IDT Microsensors	359
13.1 Introduction	359
13.2 Saw Device Modeling via Coupled-mode Theory	360
13.3 Wireless SAW-based Microsensors	364
13.4 Applications	367
13.4.1 Strain Sensor	367
13.4.2 Temperature Sensor	371
13.4.3 Pressure Sensor	375
13.4.4 Humidity Sensor	376
13.4.5 SAW-Based Gyroscope	380
13.5 Concluding Remarks	395
References	395
14 MEMS-IDT Microsensors	397
14.1 Introduction	397
14.2 Principles of a MEMS-IDT Accelerometer	398
14.3 Fabrication of a MEMS-IDT Accelerometer	399
14.3.1 Fabrication of the SAW Device	401
14.3.2 Integration of the SAW Device and Seismic Mass	402
14.4 Testing of a MEMS-IDT Accelerometer	402
14.4.1 Measurement Setup	403
14.4.2 Calibration Procedure	404
14.4.3 Time Domain Measurement	405
14.4.4 Experimental	406
14.4.5 Fabrication of Seismic Mass	408
14.5 Wireless Readout	412
14.6 Hybrid Accelerometers and Gyroscopes	414
14.7 Concluding Remarks	416
References	416
15 Smart Sensors and MEMS	417
15.1 Introduction	417
15.2 Smart Sensors	421
15.3 MEMS Devices	434
15.4 Concluding Remarks	442
References	443

Appendices	
A. List of Abbreviations	445
B. List of Symbols and Prefixes	449
C. List of Some Important Terms	455
D. Fundamental Constants	457
E. Unit Conversion Factors	459
F. Properties of Electronic & MEMS Metallic Materials	461
G. Properties of Electronic & MEMS Semiconducting Materials	463
H. Properties of Electronic & MEMS Ceramic and Polymer Materials	465
I. Complex Reciprocity Relation and Perturbation Analysis	467
J. Coupled-mode Modeling of a SAW Device	477
K. Suggested Further Reading	481
L. Webography	487
M. List of Worked Examples	491
Index	493

1

Introduction

1.1 HISTORICAL DEVELOPMENT OF MICROELECTRONICS

The field of microelectronics began in 1948 when the first transistor was invented. This first transistor was a point-contact transistor, which became obsolete in the 1950s following the development of the bipolar junction transistor (BJT). The first modern-day junction field-effect transistor (JFET) was proposed by Shockley (1952). These two types of electronic devices are at the heart of all microelectronic components, but it was the development of integrated circuits (ICs) in 1958 that spawned today's computer industry.

IC technology has developed rapidly during the past 40 years; an overview of the current bipolar and field-effect processes can be found in Chapter 4. The continual improvement in silicon processing has resulted in a decreasing device size; currently, the minimum feature size is about 200 nm. The resultant increase in the number of transistors contained within a single IC follows what is commonly referred to as *Moore's law*. Figure 1.1 shows that in just 30 years the number of transistors in an IC has risen from about 100 in 1970 to 100 million in 2000. This is equivalent to a doubling of the number per chip every 18 months. Figure 1.1 plots a number of different common microprocessor chips on the graph and shows the clock speed rising from 100 kHz to 1000 MHz as the chip size falls. These microprocessors are of the type used in common personal computers costing about €1000 in today's prices¹.

Memory chips consist of transistors and capacitors; therefore, the size of dynamic random access memories (DRAM) has also followed Moore's law as a function of time. Figure 1.2 shows the increase of a standard memory chip from 1 kB in 1970 to 512 MB in 2000. If this current rate of progress is maintained, it would be possible to buy for €1000 a memory chip that has the same capacity as the human brain by 2030 and a memory chip that has the same brain capacity as everyone in the whole world combined by 2075! This phenomenal rise in the processing speed and power of chips has resulted first in a computer revolution and currently in an information revolution. Consequently, the world market value of ICs is currently worth some 250 billion euros, that is, about 250 times their processing speed in hertz.

¹ 1 euro (€) is currently worth about 1 US dollar.